

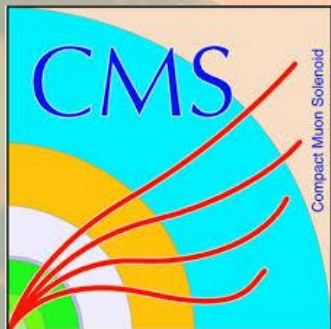


CMS HG-CAL

FEE 2016 - Krakow

Damien Thienpont on behalf of the HGC collaboration

June 3, 2016



Trigger/HLT/DAQ

- Track information in Trigger (hardware)
- Trigger latency $12.5 \mu\text{s}$ - output rate 750 kHz
- HLT output 7.5 kHz

Barrel EM calorimeter

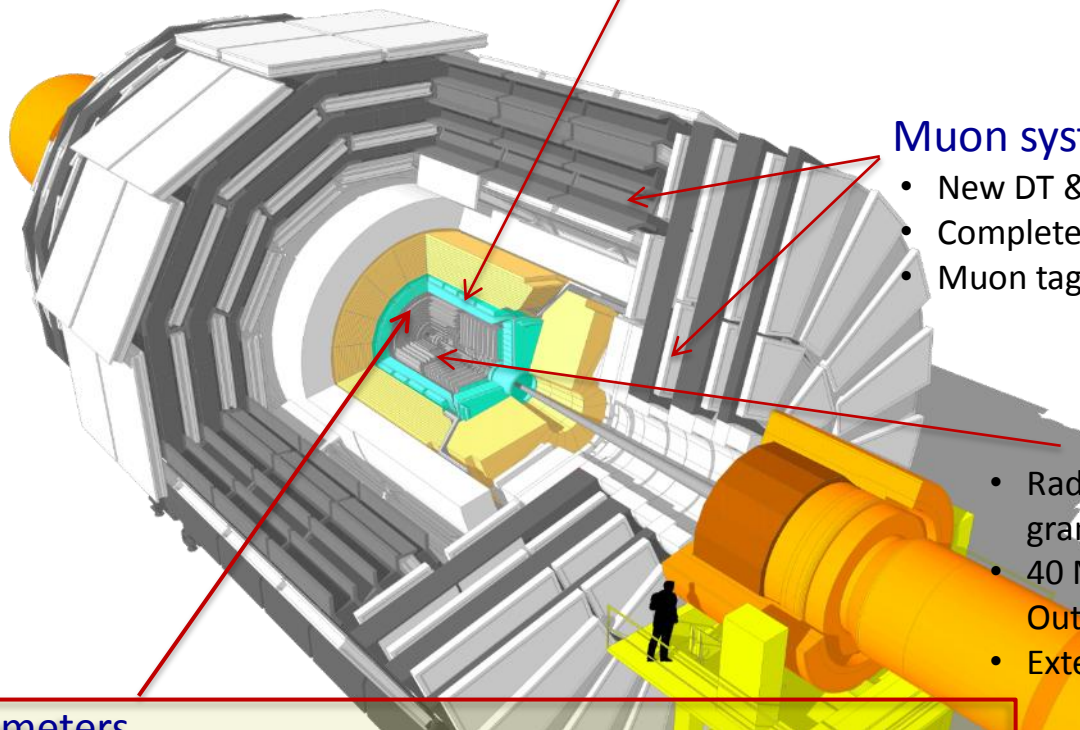
- New FE/BE electronics with improved time resolution
- Lower operating temperature (8°)

Muon systems

- New DT & CSC FE/BE electronics
- Complete RPC coverage $1.6 < \eta < 2.4$
- Muon tagging $2.4 < \eta < 3$

New Tracker

- Rad. tolerant - increased granularity - lighter
- 40 MHz selective readout in Outer Tracker for Trigger
- Extended coverage to $\eta \approx 3.8$

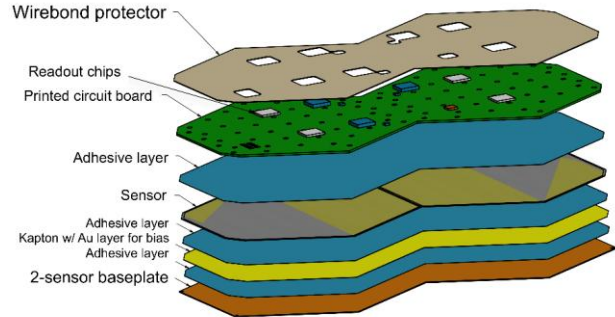


New Endcap Calorimeters

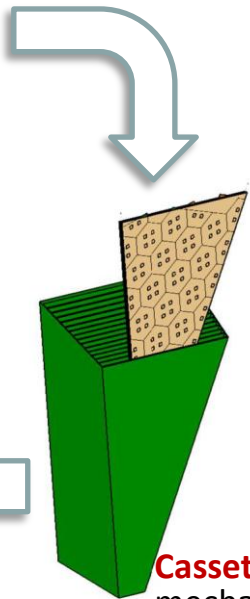
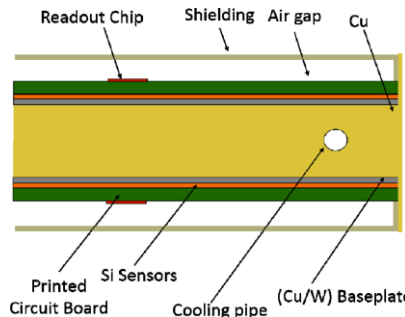
- Rad. tolerant
- High Granularity: increased transverse and longitudinal segmentation, needed to mitigate pileup effects to select events with a hard scatter process at L1-Trigger and to identify the associated vertex and particles
- precise timing capability: further mitigation of pileup effects

Modules

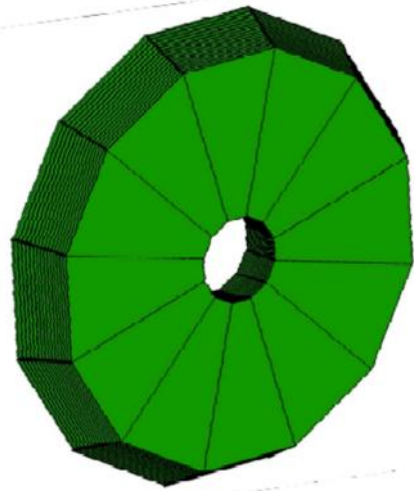
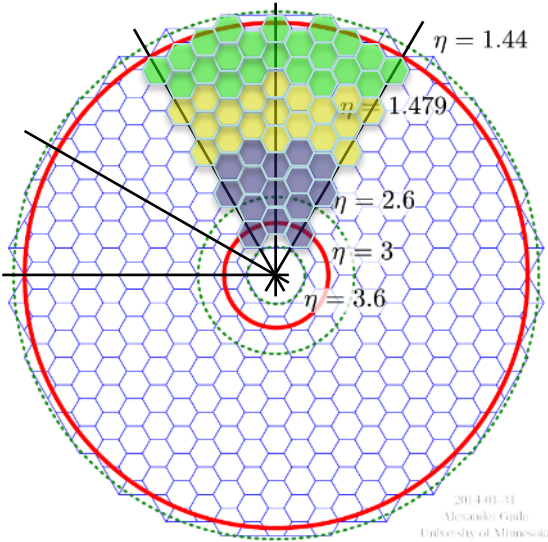
With 2x 6 - 8" Hexagonal Si sensors, PCB, FE chip, on W/Cu baseplate



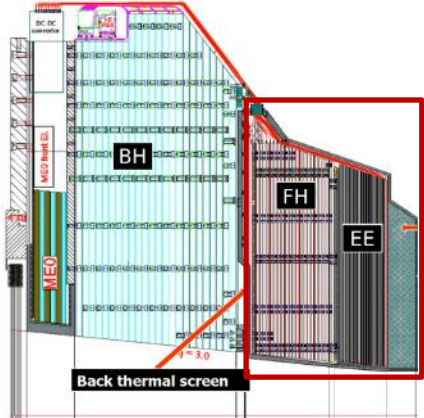
Modules mounted on Cu Cooling plate with embedded pipe
=> **Cassettes**



Cassette inserted in mechanical structure (containing absorber)



12 **Cassettes** mounted together to form the **ECAL (EE)** and **Front HCal (FH)**

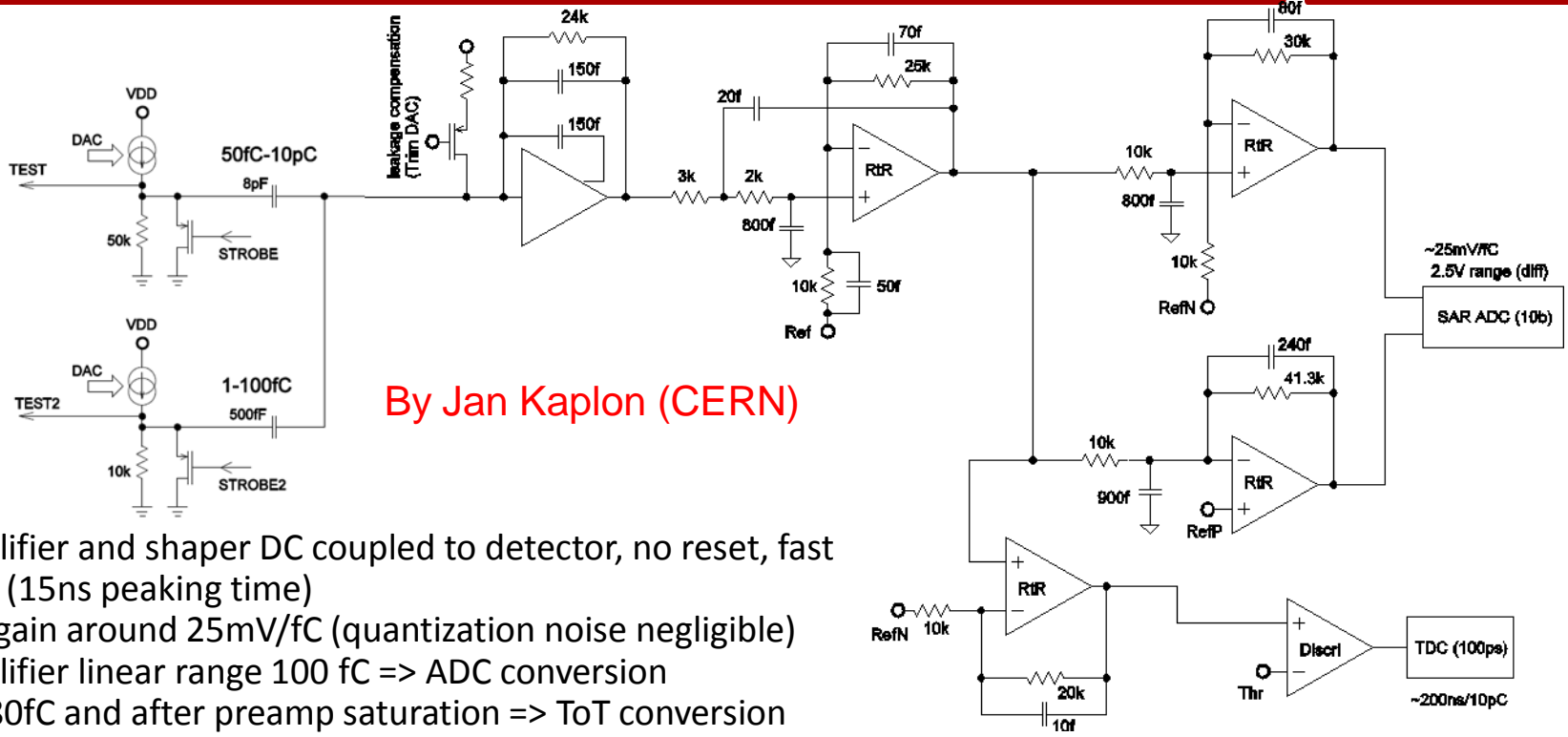


Replaced EndCap (maintained at -30°C)

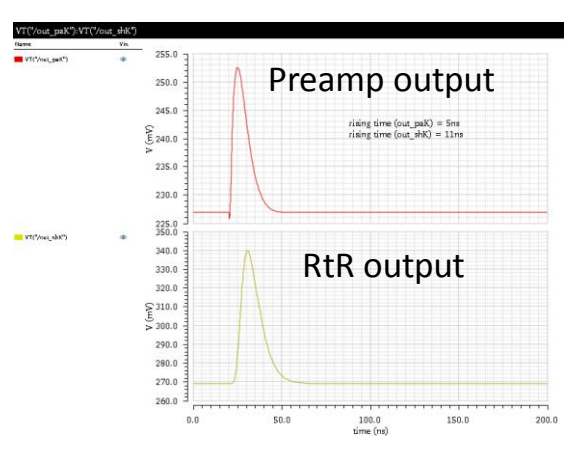
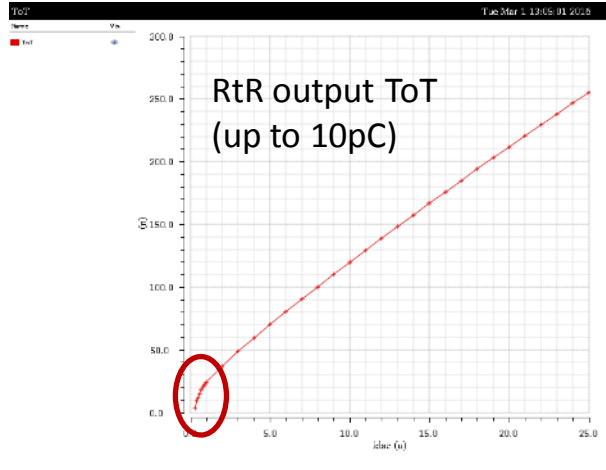
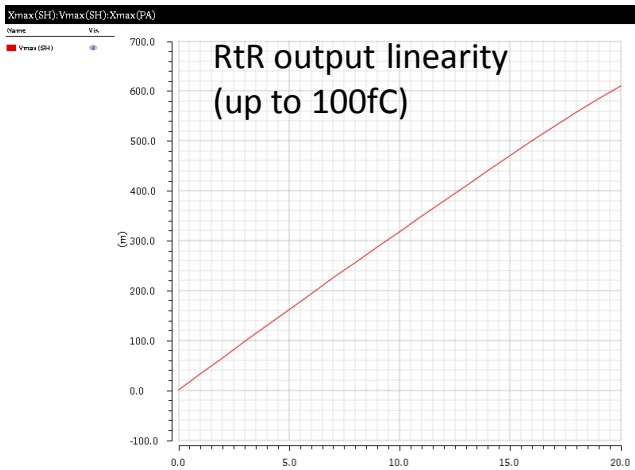
3 sensor active thicknesses 100-200-300 μm
0.5(1) cm² pads for 100(200/300) μm

- Reading out full data or largest possible sub-set **at 40 MHz** for L1-Trigger
- Stringent requirements for Front-End Electronics
 - **Low power** (~ 5 mW for analogue channel), $\sim 92\,000$ FE chips, 130 nm or 65 nm
 - **Low noise**: < 2000 e $^-$ (0,32 fC)
 - MIP: 7k – 20k e $^-$ (**1 – 3 fC**)
 - Dynamic range up to 3000 MIP (**10 pC**), **17 bits** required with 0,1 fC resolution
 - Detector capacitance **40-60pF**, detector leakage: up to **10 μ A**
 - **System on chip** (charge, time, digitization, data and trigger processing, on-chip zero suppress, ...)
 - **High speed readout** (5-10 Gb/s)

Baseline architecture (Technical Proposal)



- Preamplifier and shaper DC coupled to detector, no reset, fast shaping (15ns peaking time)
- Analog gain around 25mV/fC (quantization noise negligible)
- Preamplifier linear range 100 fC => ADC conversion
- Above 80fC and after preamp saturation => ToT conversion

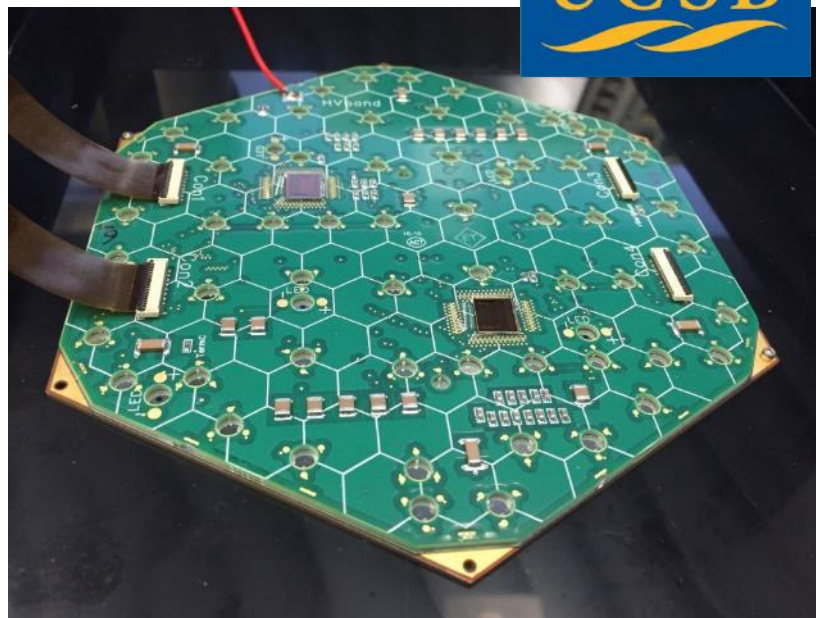


- 15-Feb-16 **Submit v0 FE chip (SKIROC2-CMS) in 0,35 μm** ⇒ Part 1
- Mid-May-16 **Submit FE test vehicles in TSMC130 nm technology** ⇒ Part 2
- 1-Jun-16 1st Comprehensive Review
- 30-Sep-16 **1st results from FE test vehicles and second test vehicle submission**
- 31-Oct-16 Confirm choice of front-end electronics (130 nm)
- 15-Dec-16 Define architecture & specs for LV/HV supply
- 15-Dec-16 Define location of DC-DC converters
- 15-Dec-16 Define location of electrical/optical links

- 31-Mar-17 **Submit V1 ASIC** ⇒ First 32/64 ch ASIC with full fonctionnality
- 31-Mar-17 Choice of Si sensors type: all n-on-p or mixed (i.e. n-on-p and p-on-n)
- 1-Jun-17 2nd Comprehensive Review
- 30-Sep-17 1st results from tests of V1 ASIC
- 1-Nov-17 Submit TDR

- 30-Jun-18 **Submit V2 ASIC**

- Testbeam electronics
 - Use SKIROC2 to exercise system issues (low noise, large range)
 - Complex front-end boards designed at UCSB, Minnesota, FNAL : delicate routing
 - Evolutive readout designed at FNAL
- Development of **SKIROC2-CMS**
 - **Optimized version for CMS test beams**, pin to pin compatible
 - Dual polarity charge preamplifier
 - Faster slow shaper (25ns instead of 200ns)
 - SCA in roll mode (sampling of slow shapers @ 40MHz, depth = 300ns)
 - ToT for high input charge
 - TDC (TAC) for ToA (~20 ps binning, ~50ps jitter)
 - Will replace SKIROC2 on modules for **timing and ToT studies**



This “little” setup has ~14k ch. to read out !

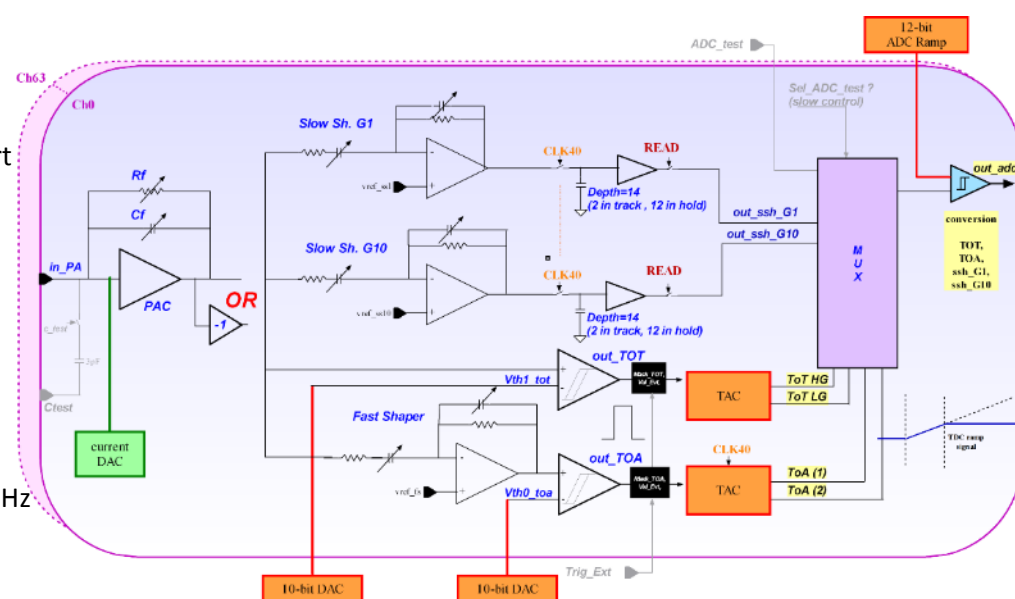
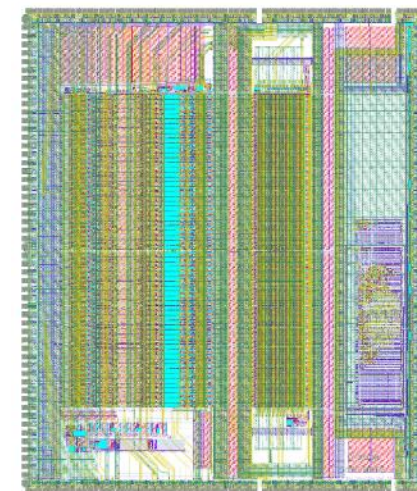
- Input DAC and 3pF calibration Cap.
- Versatile preamplifier
 - Dual polarity: single first stage with **input PMOS transistor** (available NMOS are directly on substrate), one feedback for each polarity (likely better for positive input charge), high dynamic range optimization
 - **60 dB** Open loop gain, **4 GHz** GBWP
 - **Variable Rf**: global 8 bits, from 10k to 2,55M
 - **Variable Cf**: global 6 bits, from 62fF to 4pF
- Charge measurement in 12 deep SCA
 - Slow shapers: gain 1 and 10, CRRC2; variable shaping time: global 4 bits, from 10ns to 150ns; output buffer
 - 2 measurements by BX, HG and LG
 - Nominal: roll mode @ 40MHz; custom mode: managed by external trigger
- Charge measurement with ToT for signal after peamp saturation
 - Discriminator connected to the preamp output
 - Fast ramp dedicated to the special study of the non-linear part
 - Slow ramp for the entire range (up to 10pC)
 - ToT data are memorized into the feedback capacitance of the integrator, rising edge starts the ramp and falling edge stop it
- Time measurement
 - Fast shaper: CRRC, gain 6, shaping time: 3bits, 1,25 to 9ns
 - Fast discrimi
 - Ramp: 35ns, rising edge starts the ramp
 - Time SCA: 2 holds done on rising and falling edges of the 40MHz
- Analogue to digital conversion
 - 12 bits Wilkinson ADC, common ramp

POWER CONSUMPTION

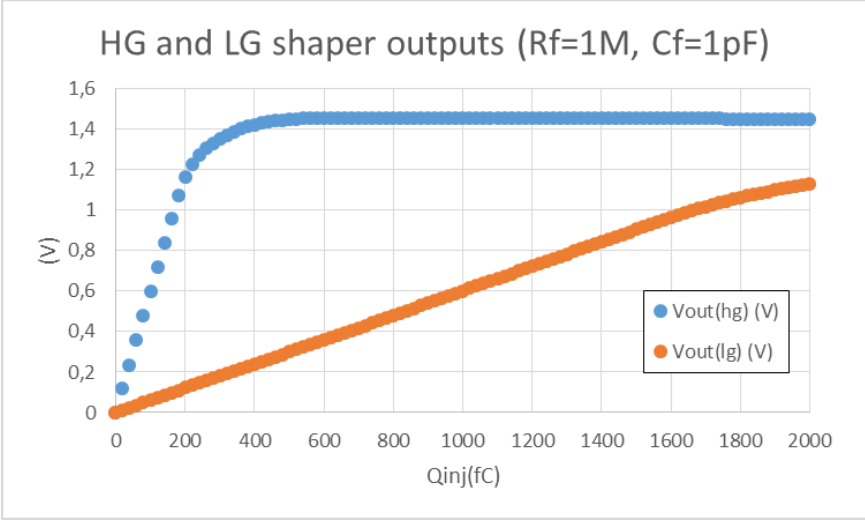
Preamplifiers (positive / negative)	5,3 mW / 5,6 mW
Slow shapers	1,94 mW
ToT	0,1 mW
ToA	2,6 mW
TDC	1,93 mW
Total analog (/channel)	12 – 13 mW

Assuming 20mW power dissipation for the digital part, we expect 850 mW for the entire chip

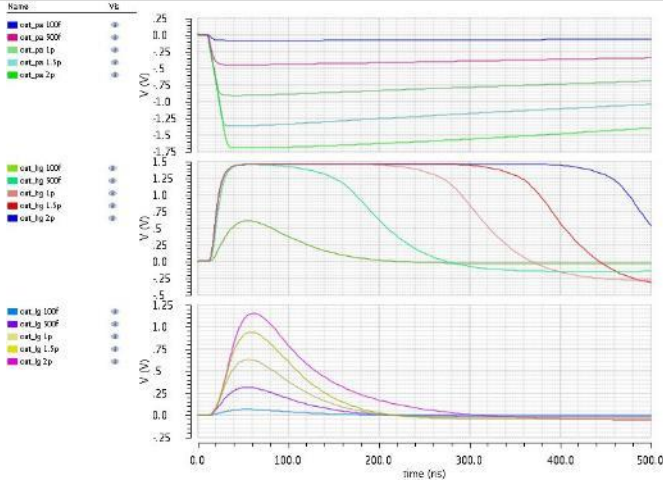
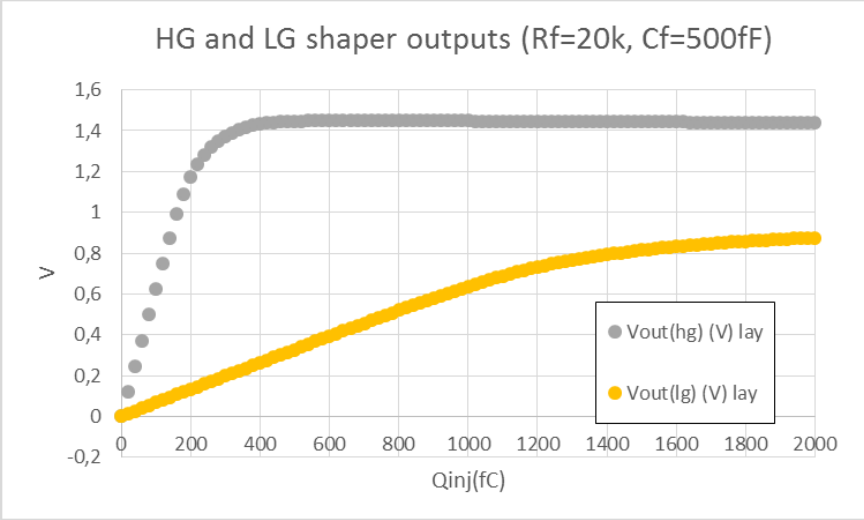
SKIROC2-CMS



Charge PA
Rf=1M, Cf=1pF



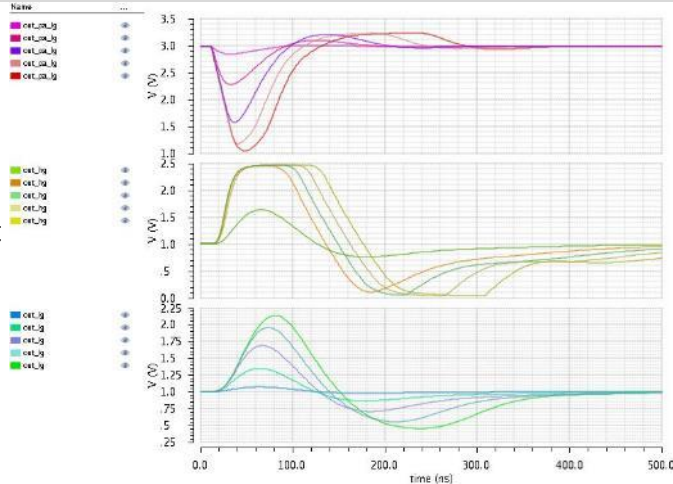
Current PA
Rf=20k, Cf=500fF



Preamp output

HG shaper output

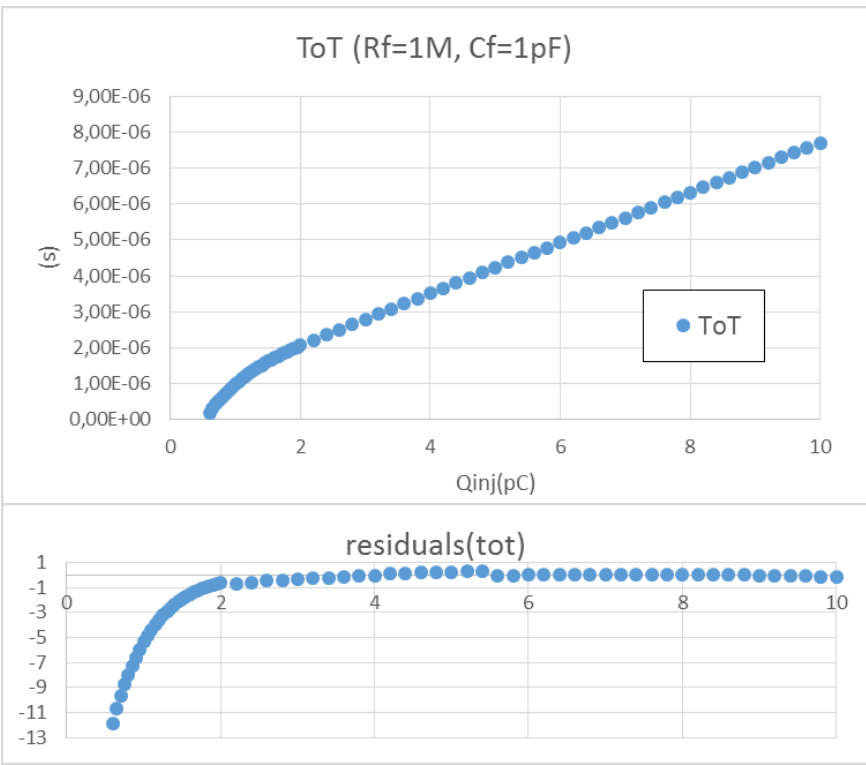
LG shaper output



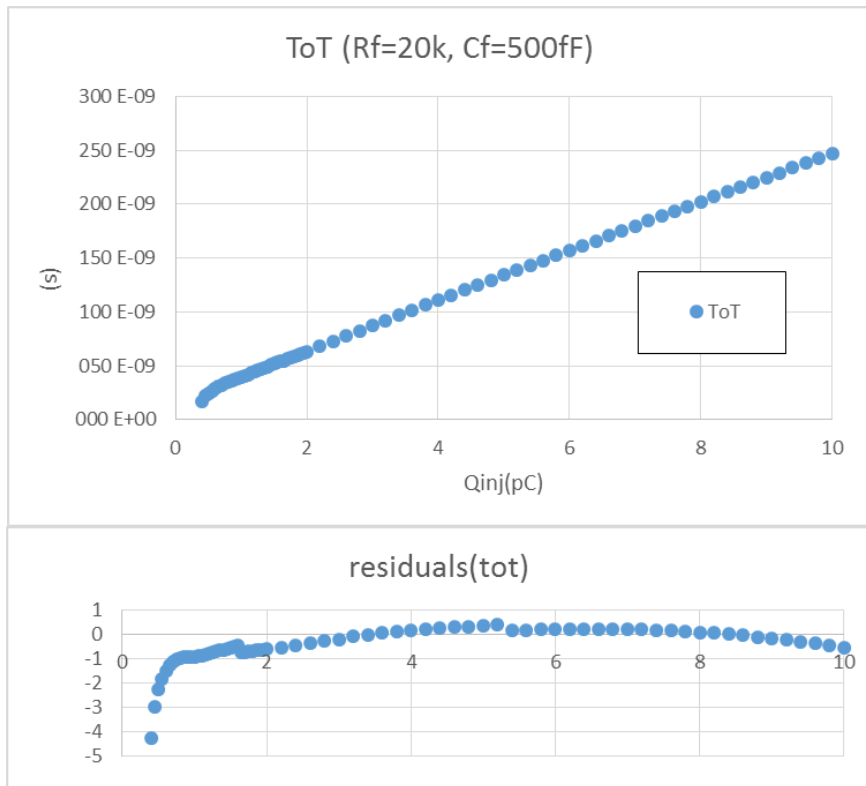
- HG linearity: from 0 to 180 fC
- LG linearity: from 0 to 1750 fC

- HG linearity: from 0 to 160 fC
- LG linearity: from 0 to 950 fC

Charge PA
Rf=1M, Cf=1pF



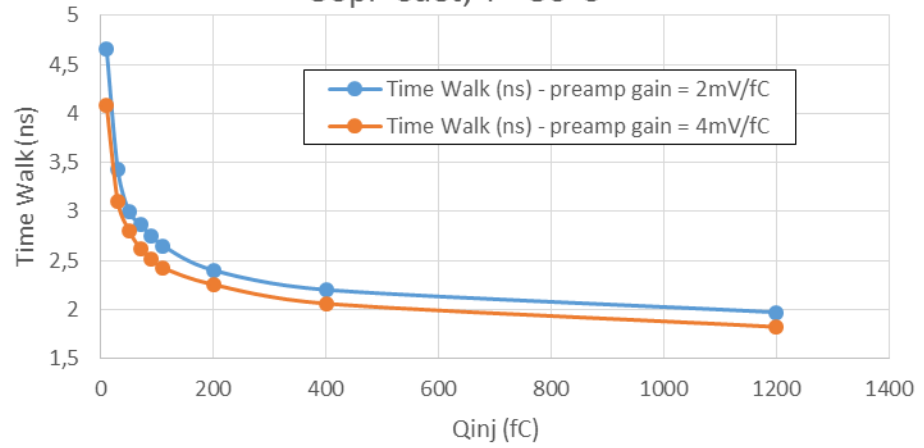
Current PA
Rf=20k, Cf=500fF



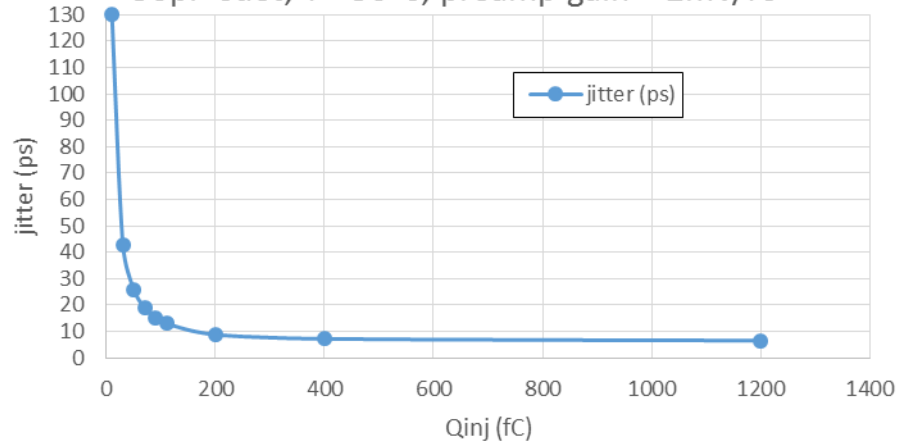
- Threshold @ 700 fC
- Good ToT linearity: from 1,75 pC to 10 pC

- Threshold @ 450 fC
- ToT linearity: from 1,7 pC to 10 pC

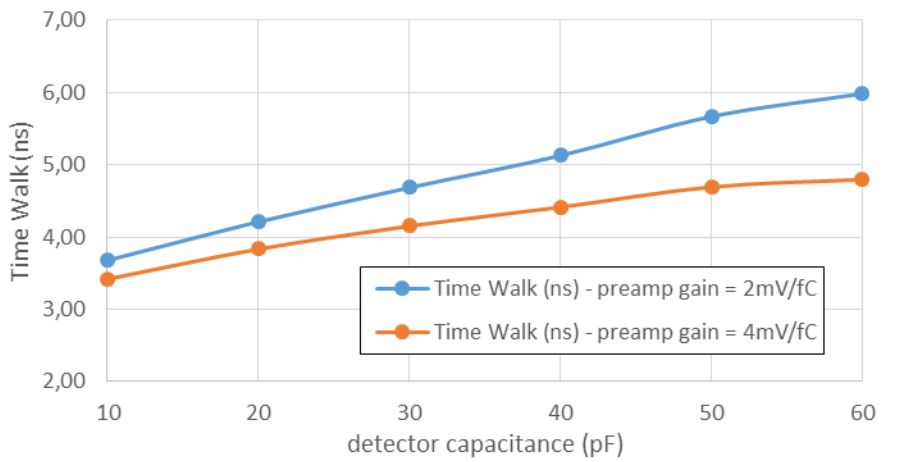
Time Walk (ns)
30pF Cdet; T=-30°C



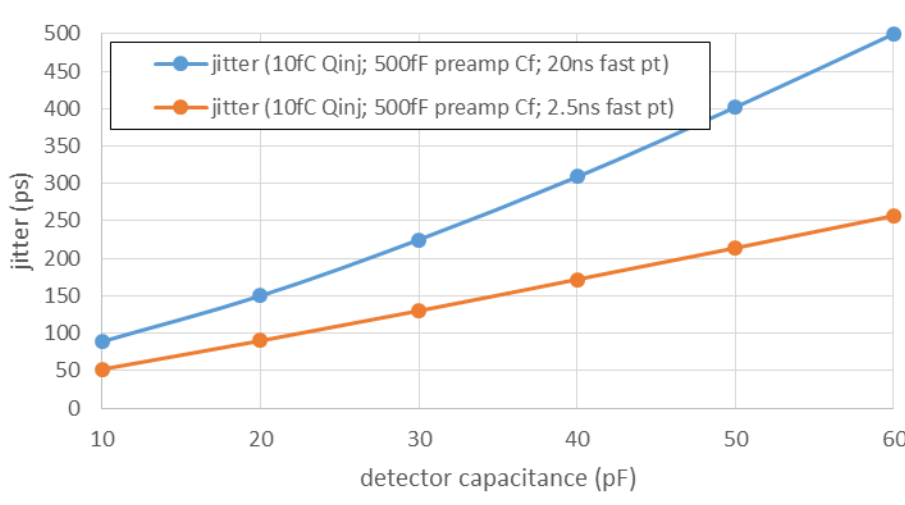
jitter (ps)
30pF Cdet; T=-30°C; preamp gain = 2mV/fC



Time Walk
10fC injected charge



jitter @10fC injected wrt. Cdet



Digital readout scheme

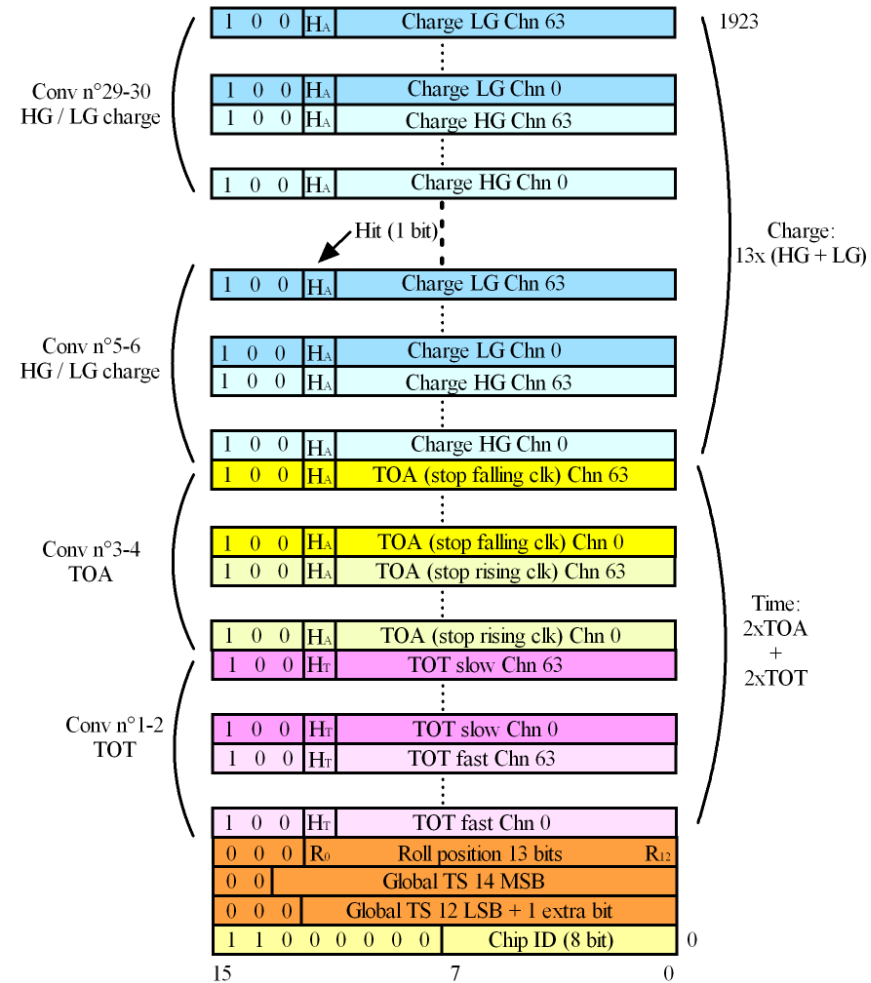
- Based on Calice chips readout scheme



- Roll mode @ 40MHz
- depth $12 \times 25\text{ns} = 300\text{ns}$

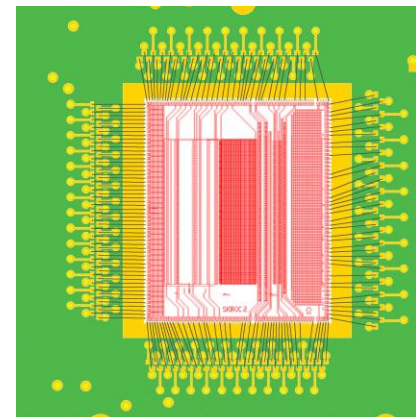
- 12-bit Wilkinson ADC, starts on external Trigger
- 2 ToT (fast & slow); 2 ToA; 2x12 HG & LG Charge
- Duration (worst case) = $2^{12} \times 25\text{n} \times 30 = 3\text{ ms}$

- OC @ 5MHz (SK2) to LVDS @ 40MHz (SK2-CMS)
- Cst. $1924 \times 16 \times 25 = 770\mu\text{s}$



- HGC targeted Skiroc2-CMS chip variant with
 - n-on-p as well as p-on-n read-out
 - LHC-like ~ 20 ns shaping time
 - Leakage current compensation for irradiated sensors
 - Key features and variants of HGC FE architecture
 - Including TDC for precision timing and ToT
 - Pin-to-pin compatible
 - Design submitted, expect chips back in Spring
- SKIROC2-CMS aims
 - ToT scheme non linear in region 100-200fc: needs precise calibration and demonstration in Test-beam
 - Will be studied with SKIROC2-CMS and test vehicle
 - Backup with bi-gain and ToT above 1-2 pC or dynamic gain switching
- January 2016: first fully functional Si-HGC modules equipped with existing SKIROC2 chips
 - Skiroc2 designed for p-on-n sensors, but too slow shaping time, readout based on Calice requirements
- Spring 2016: test beams at FNAL with Si-HGC EE slice equipped with Skiroc2
 - Enable tests of EM calorimetric response
 - Prepare for more detailed studies using modules equipped with Skiroc2-CMS
- **Fall 2016: test beams at CERN** with Si-HGC EE and FH slice equipped with Skiroc2-CMS
 - Enable detailed studies of calorimetric response and performances of baseline architecture and variants
 - Aim for timing studies of EM and Hadronic shower evolution with ~ 50 ps calorimeter cell timing resolution

Landing of SKIROC2(-CMS)
Designed at UCSB



- Area: 2,2x1,36 mm²
- 101 PADs, 100μm pitch
- Power supply: 1,2 – 1,5 V
- Submission date: mid-may 2016

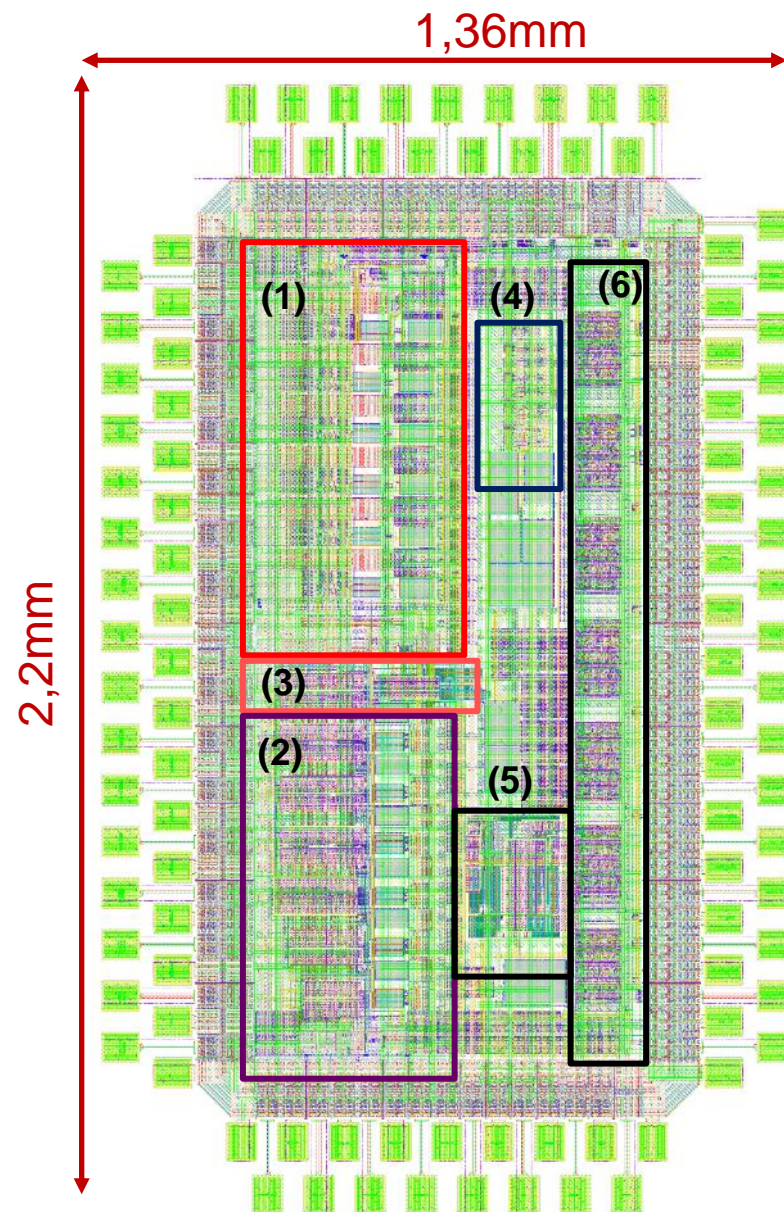
- Floorplan

- (1) positive input preamps x6
- (2) negative input preamps x6
- (3) baseline channel (CERN) x1
- (4) discriminators x4
- (5) CRRC shapers: HG and LG
- (6) digital part

- Available outputs

- Direct preamp output
- Preamp after shaper
- Preamp after discriminator

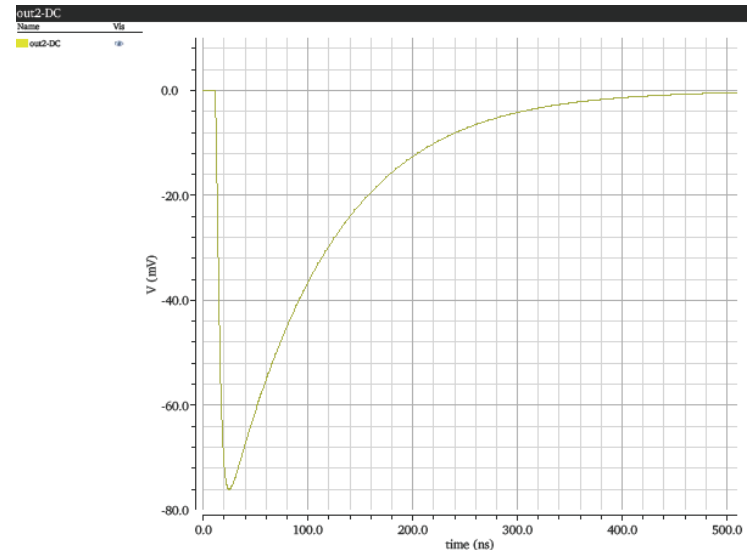
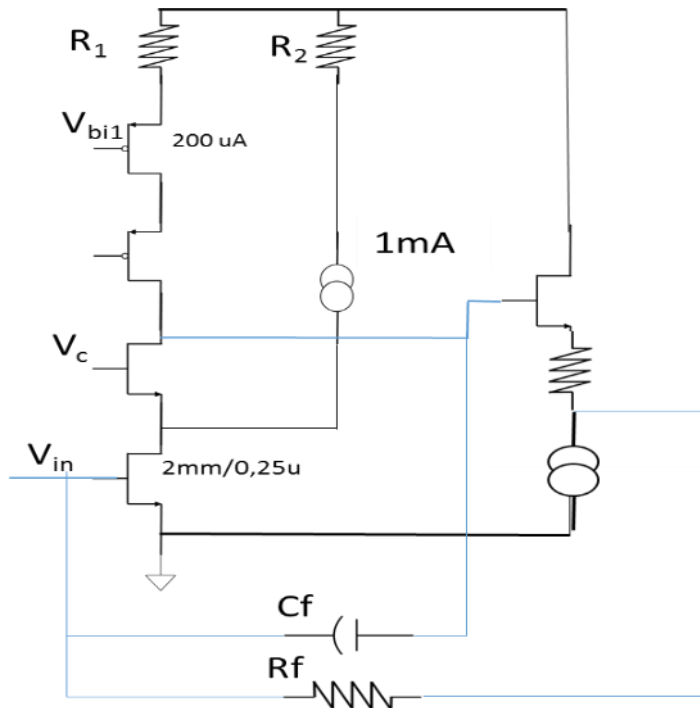
- Dedicated PAD available to characterize the shapers or the discriminators
- All bias can be externally tuned



Input NMOS transistor preamplifier for positive signal

- 6 different preamps for positive signals
- Based on a cascode architecture
- Used different NMOS sizes (1200 μ , 2400 μ , 3600 μ) and transistor flavors proposed by the technology (“normal”, “HiVt”, “LoVt”)
- Variable Cf from 100fF to 1,5pF step 100fF
- Variable Rf: 20k, 200k and 1M Ω
- Optimize to get open loop gain above 60dB and minimize noise
- Power consumption: \sim 2mW

- $e_n = 0,4 \text{ nV}/\sqrt{\text{Hz}}$
- rms noise = 210 μV
- With 50pF Cdet, after 25ns shaper, ENC \sim 1.3ke⁻

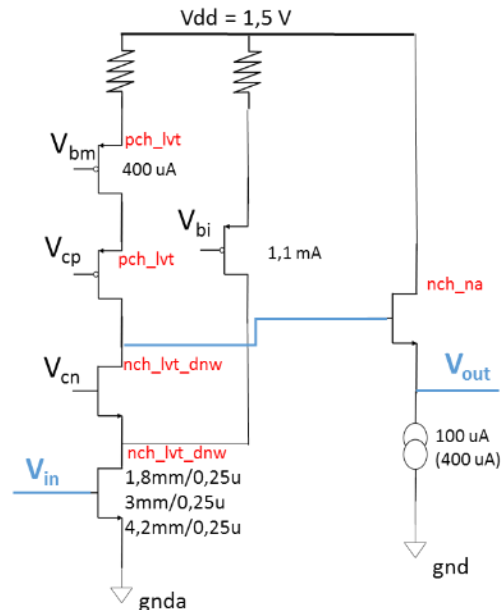


Qinj=100fC; Cd=50pF; Cf=1pF;
Rf=20k

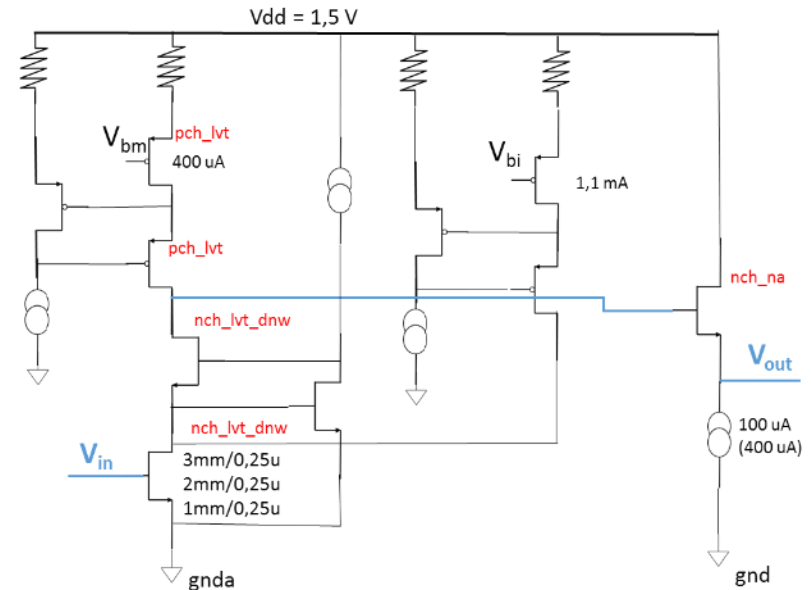
Input NMOS transistor preamplifier for negative signal

- 6 different preamps for negative signals
- Used different NMOS sizes and architectures
- Variable Cf from 100fF to 1,5pF step 100fF
- Variable Rf: 20k, 200k and 1M Ω

- With 50pF Cdet, 20k Rf, after 25ns shaper, ENC $\sim 1.2ke^-$
- With 50pF Cdet, 1M Rf, after 25ns shaper, ENC $\sim 1ke^-$



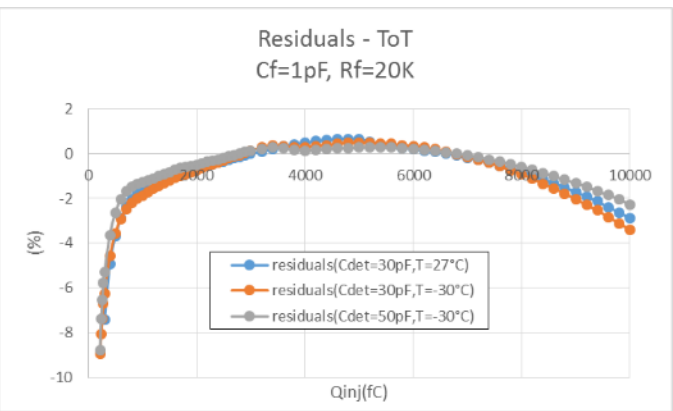
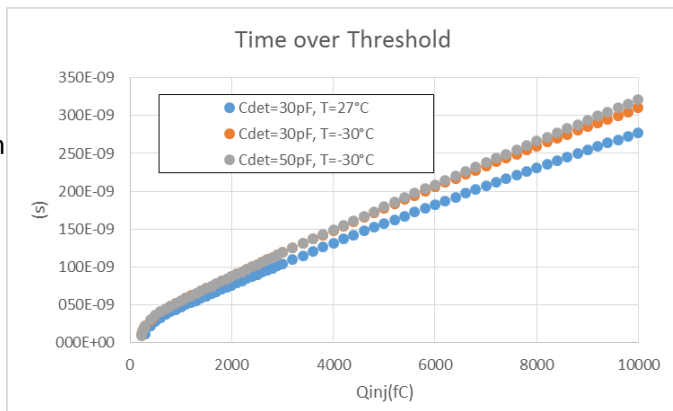
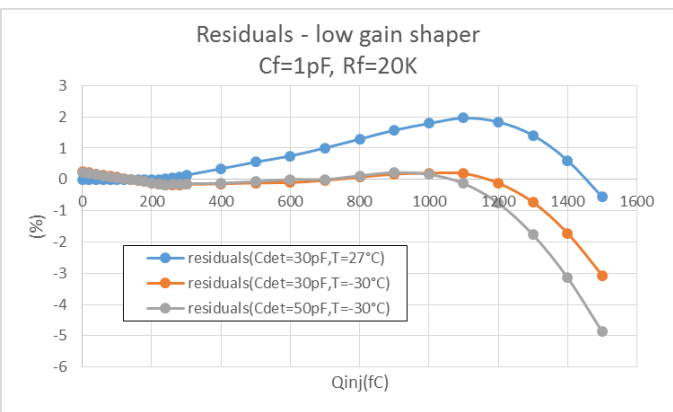
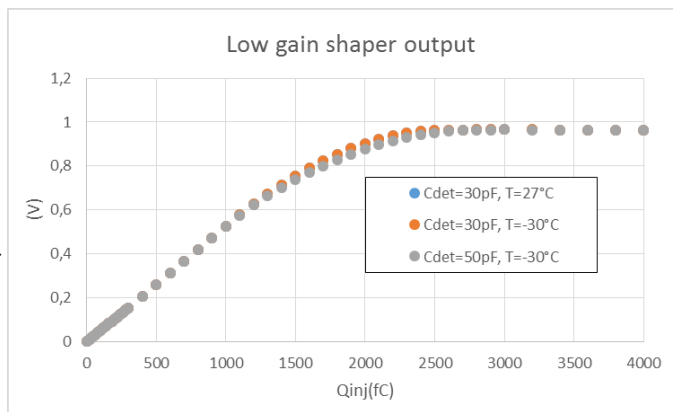
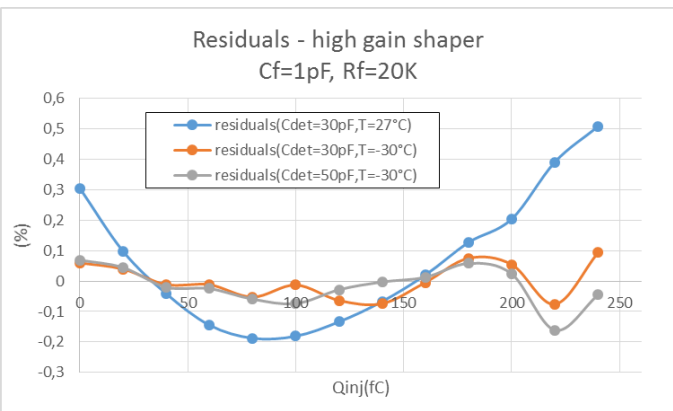
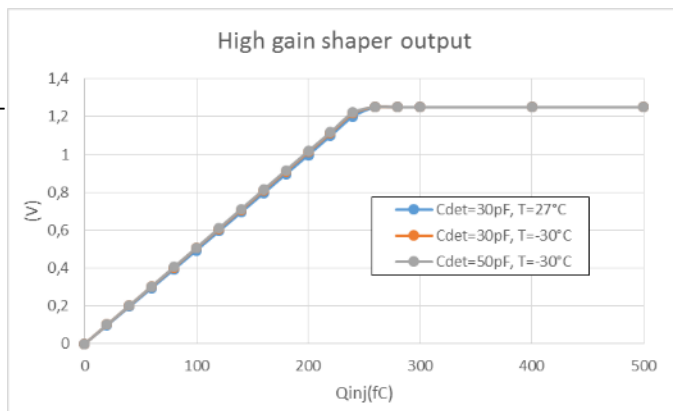
- Input stage: cascode with NMOS input transistor
- Output buffer: source follower with NMOS native transistor biased with 100 μA
- 62 dB open loop gain; 2,4 GHz GBP; Input impedance: 16 Ω (50 Ω @ 50MHz)
- Power consumption: 2,4 mW (@ 1,5V)
- Three sizes of input NMOS transistors



- Input stage: regulated cascode with NMOS input transistor
- Output buffer: source follower with NMOS native transistor biased with 100 μA
- 94 dB open loop gain; 3,5 GHz GBP; Input impedance: 0,5 Ω (43 Ω @ 50MHz)
- Power consumption: 2,85 mW (@ 1,5V)
- Well suited for high loop gain preamp (0,2pF Cf)
- Three sizes of input NMOS transistors

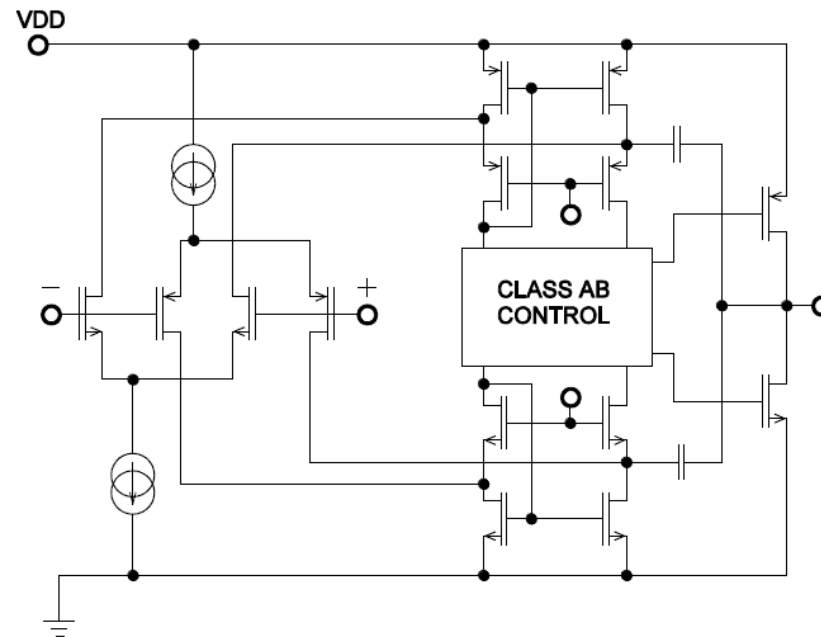
TV1: linearities

- 1pF Cf, 20K Rf, 30 and 50pF Cdet, 27 and 30 °C
- High gain:
 - linear up to 240 fC
 - Better linearity at low temperature
- Low gain:
 - Good linearity up to 1200 fC
 - Saturation occurs before with high Cdet
- Time over Threshold:
 - Threshold @ 250 fC
 - Linearity better than 1% begins around 1300 -1600 fC
 - Dependence to the temperature: 26ns/pC @ 27°C and 30ns/pC @ -30°C
 - Low dependence to Cdet: 29ns/pC @ 30pF Cdet and 30ns/pC @ 50pF Cdet



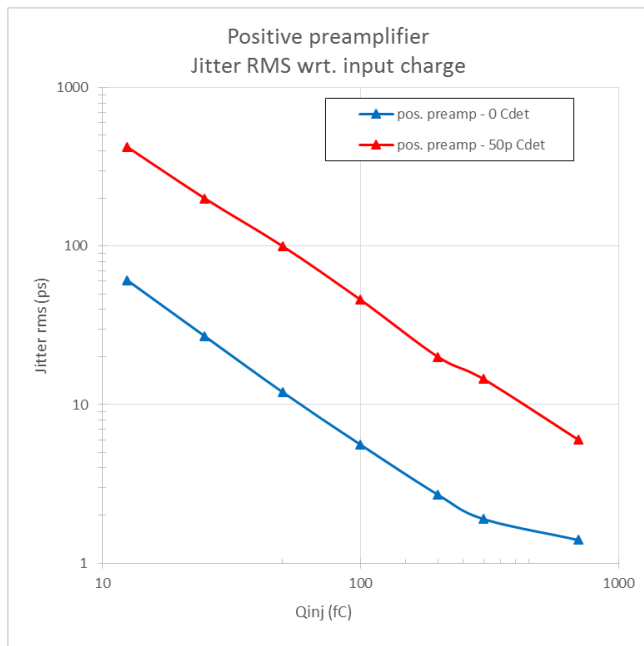
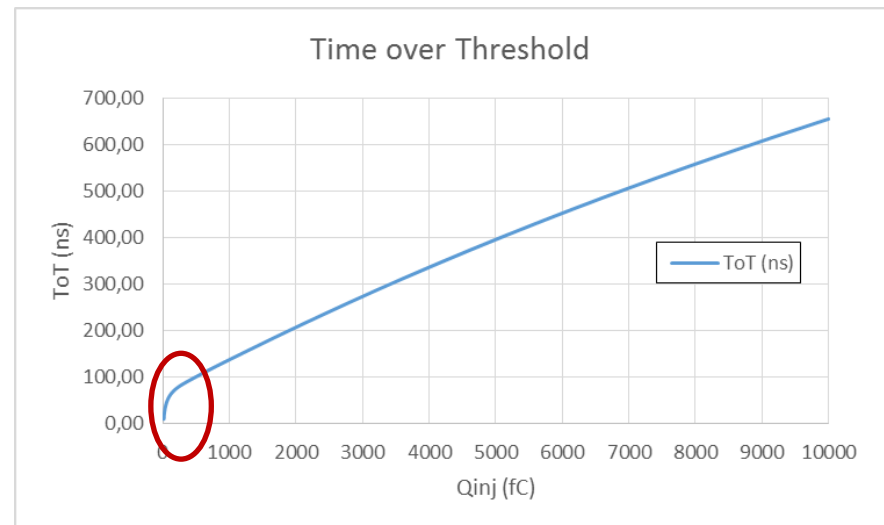
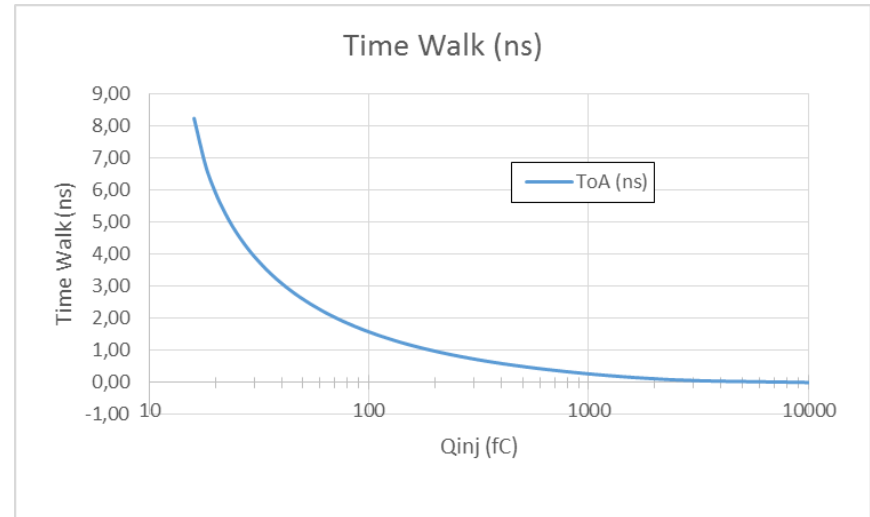
- There is never a good overlap between low gain and ToT, precise characterization is needed. It is due to the non-linear behavior when preamplifier pass through from the non-saturation mode to the saturation mode

- Rail-to-Rail class AB operational amplifier
 - Cascode-miller compensation tunable on 5 bits
- 2 shapers
 - Gain 1 and gain 10
 - Variable shaping time: global 4 bits, from 5ns to 75ns

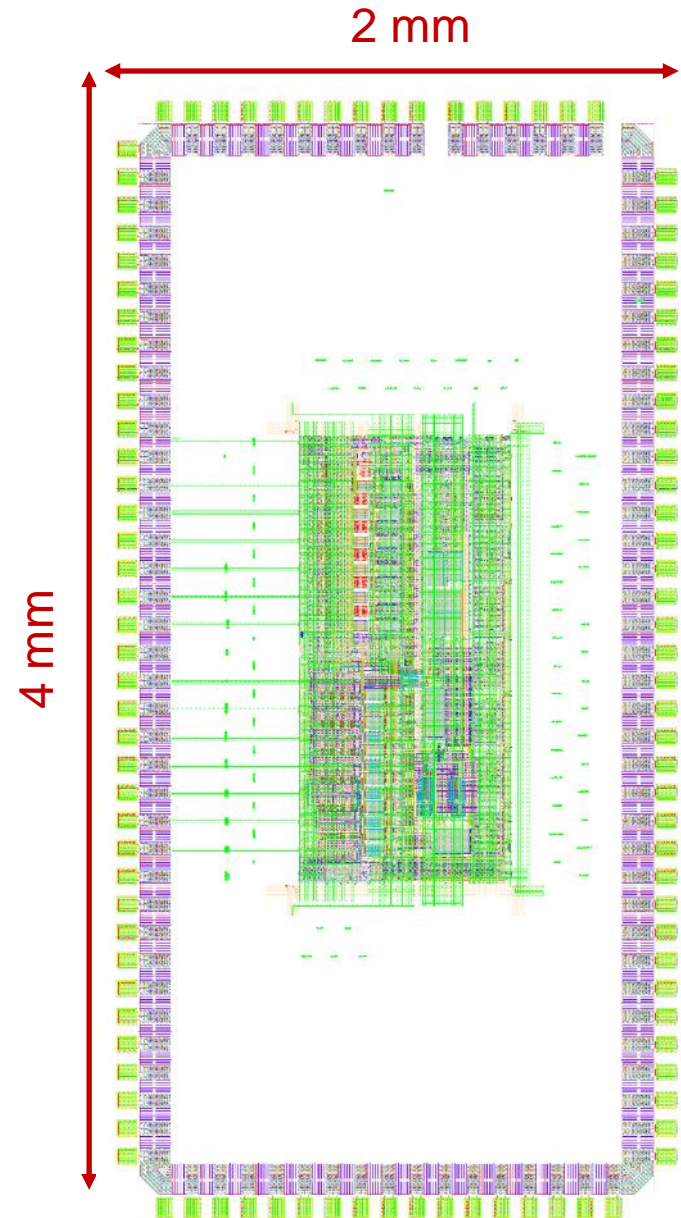
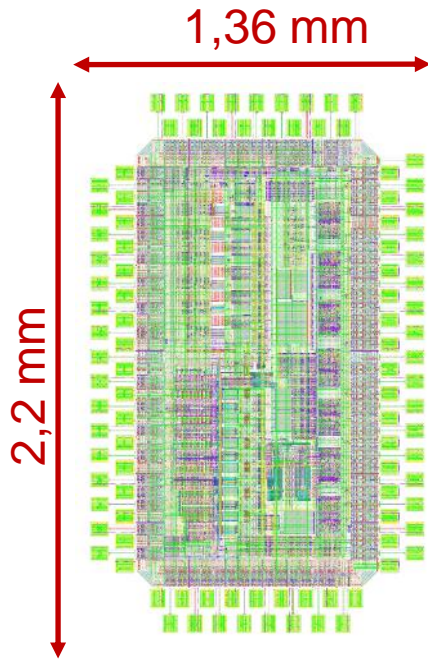


Discriminators

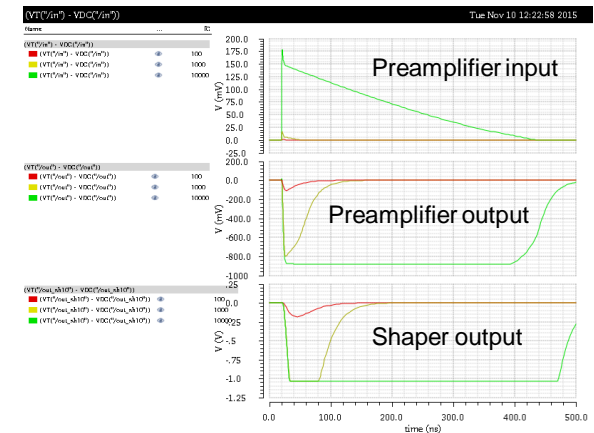
- 4 fast discriminators designed (2 designs for each polarity) for ToA, ToT and ADC
- Power consumption: $\sim 750\mu\text{W}$
- Offset: 3,5mV rms
- Time Walk
 - 6ns @ 20fC (~ 10 MIP)
 - 1,5ns @ 100fC (~ 50 MIP)
- ToT
 - Linear from 1pC to 10pC
- Jitter
 - Without detector capacitance: 60ps rms @ 10fC ($\sim 3 - 6$ MIP)
 - With 50pF detector capacitance: 400 ps rms @ 10fC (~ 5 MIP), 50 ps rms @ 100 fC (~ 50 MIP)
 - Jitter performances should be improved with a fast and high gain shaper after preamplifier



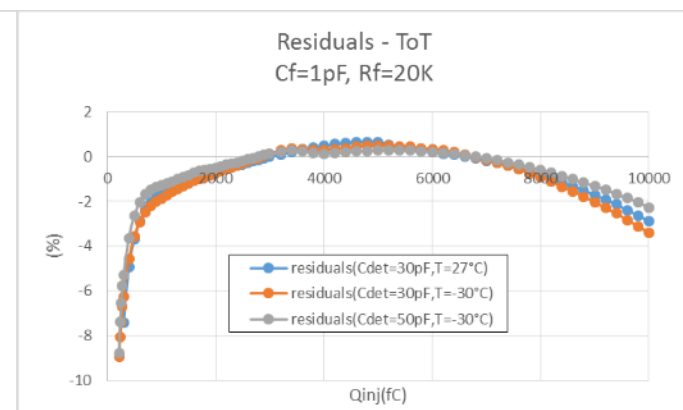
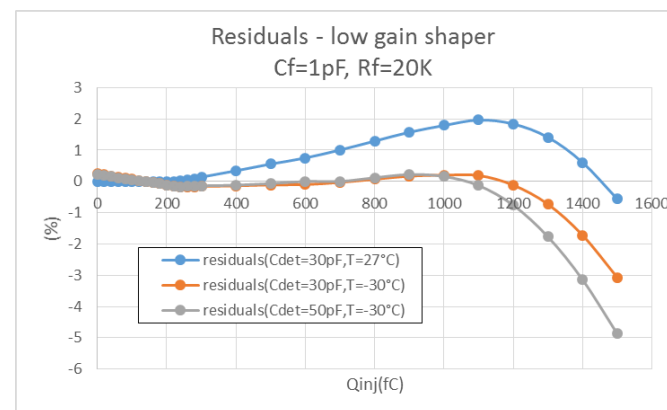
- Packaging issues
 - Wire bond angles between chip pads and package plots cannot be higher than 20°
 - Wire bond length issue
 - Finally enlarged pad ring => 2x4mm single in-line



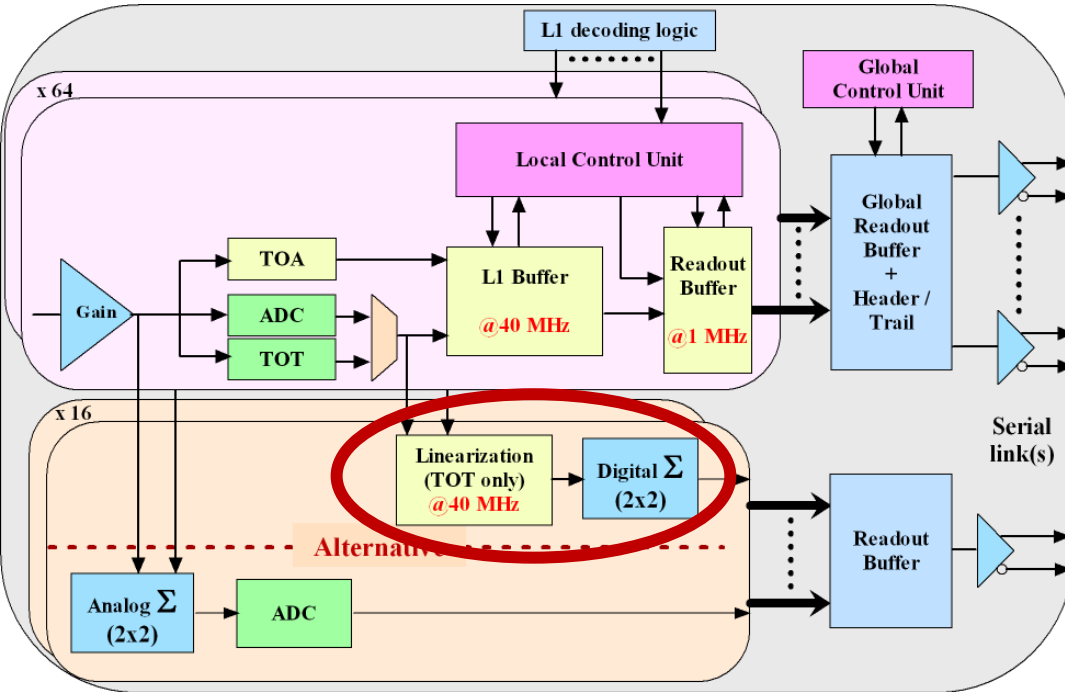
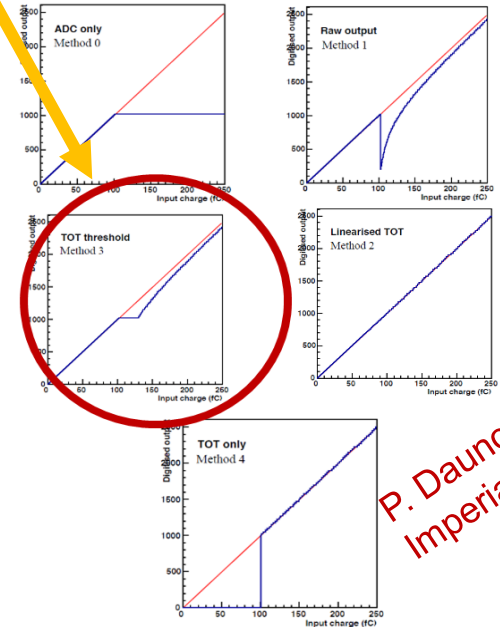
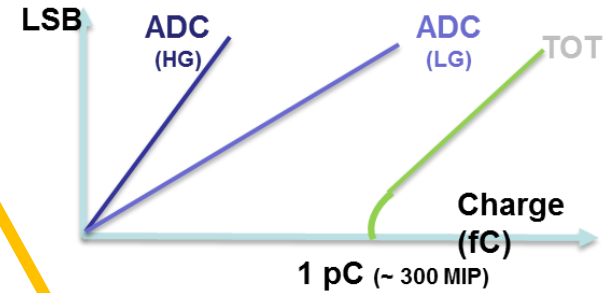
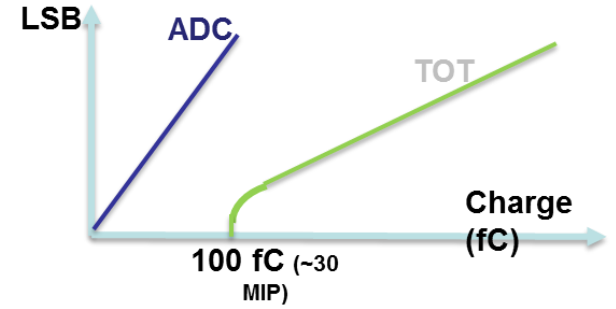
- **High crosstalk** when preamplifier is saturating
- **Long dead time** due to ToT. It depends of preamplifier feedback resistance
- There is **never a good overlap between low gain and ToT**, precise characterization is needed. It is due to the non-linear behavior when preamplifier pass through from the non-saturation mode to the saturation mode
- Trigger path has to deal with **ADC data (mV)** and **ToT data (ns)** and with a non-linear ToT behavior at the first. **The ToT data have to be linearized.**



Transient signals for 100, 1000 and 10000 fC injected charge



- ❑ Study 2x2 linearization to be ready for 2nd TV:
 - ❑ ADC data
 - ❑ TOT without non-linear region
- ❑ Focusing on “method 3”
- ❑ Solution applicable for baseline or bi-gain PA

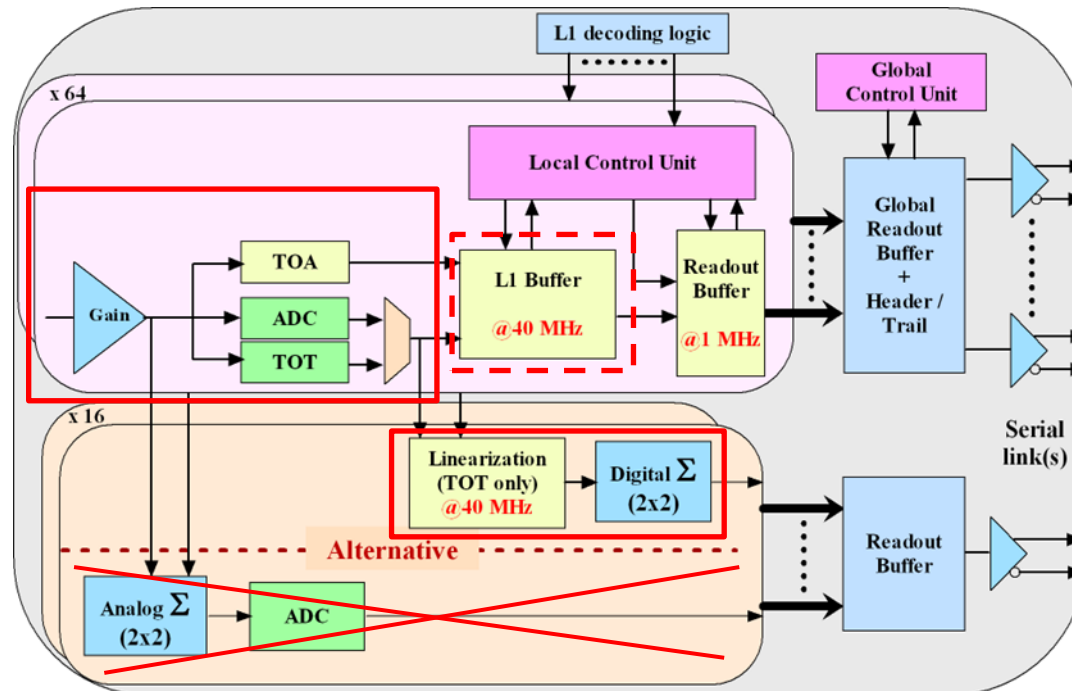


↔ Analog front-end
 ↔ ADC
 ↔ Local digital processing
 ↔ Global digital readout

What do we plan to submit in TV2 ?

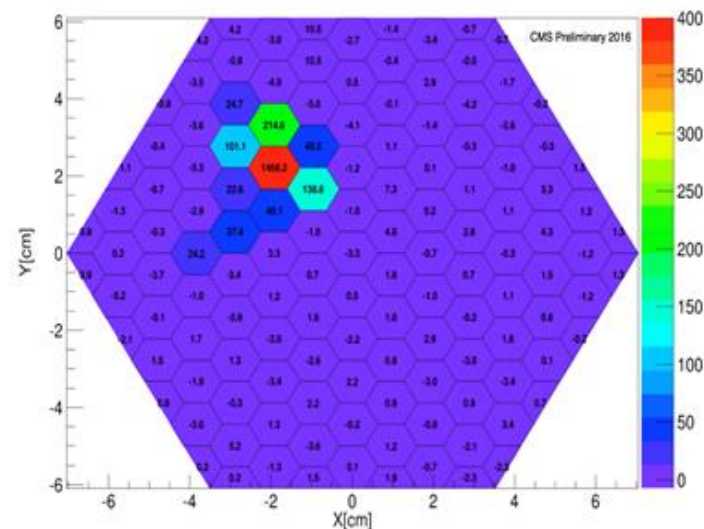
- Full analogue channel
 - Preamplifiers, shapers, comparators, input DAC (leakage compensation)
 - 10-bit ADC, 12-bit TDC
- Digital sum for trigger path
 - Linearization ToT @ 40 MHz
 - Digital sum: 2x2 cluster
 - L1 buffer for 1 MHz readout
- Common services
 - 10-bit DAC, bandgap, LVDS, PLL and DLL

September 2016



- Challenging detector
 - High speed low noise large dynamic range readout
 - High integration and large data output

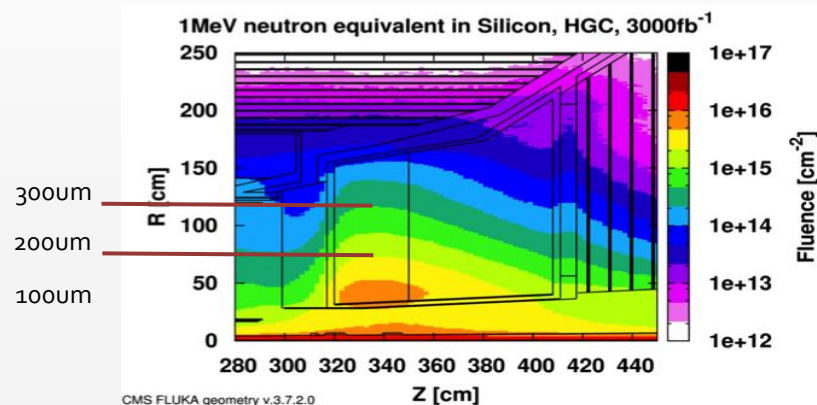
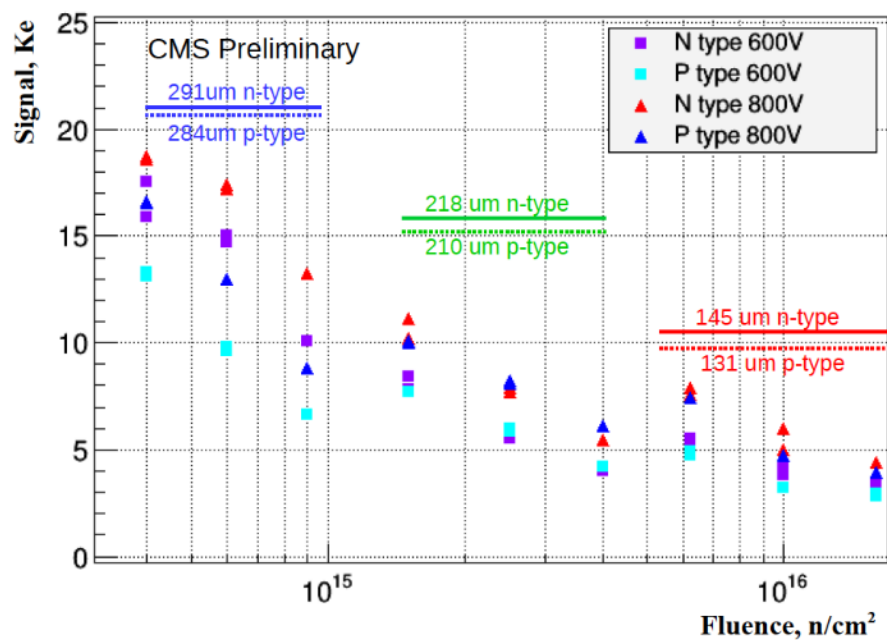
- Several issues to be studied rapidly
 - ToT accuracy. Timing performance.
 - System issues.
 - Prototypes assembled for tests in beam
 - Will be studied with SKIROC2-CMS and test vehicle
 - Backup with bi-gain and ToT above 1-2 pC or dynamic gain switching



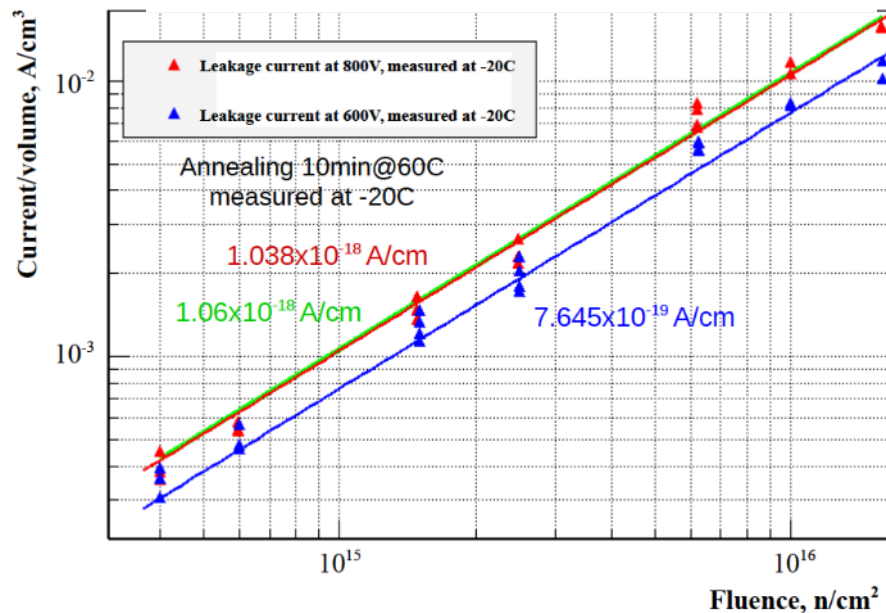


Basic Silicon sensor R&D

Essential results documented in TP



Slide From M. Mannelli,
ACES Workshop



- $C_d = 50\text{pF}$, $T = -30^\circ\text{C}$, noise after HG shaper, no leakage current

ENC	$R_f=1\text{M}, C_f=1\text{pF}$	$R_f=20\text{k}, C_f=500\text{fF}$
Positive input	0,2fC (1250 e-)	0,25fC (1560 e-)
Negative input	0,23fC (1440 e-)	0,3fC (1875 e-)

- Noise after HG shaper is dominated by input PMOS transistor

CROSSTALK

Signal	Crosstalk	Crosstalk
Preamp output	0,34%	0,35%
HG shaper	0,3%	0,7%
LG shaper	0,34%	0,35%
Fast shaper	0,62%	3% ⁽¹⁾

(1) Neighboring channels trigger when hit channel is saturating

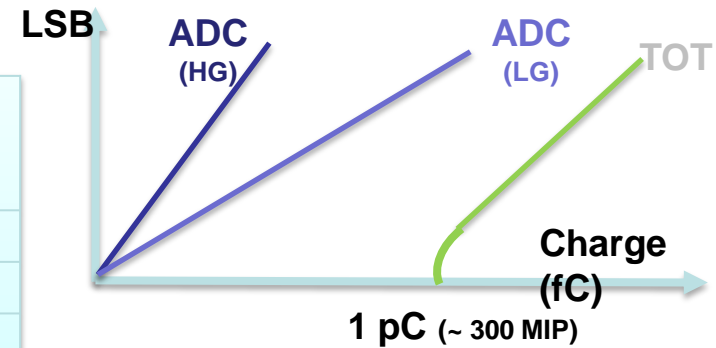
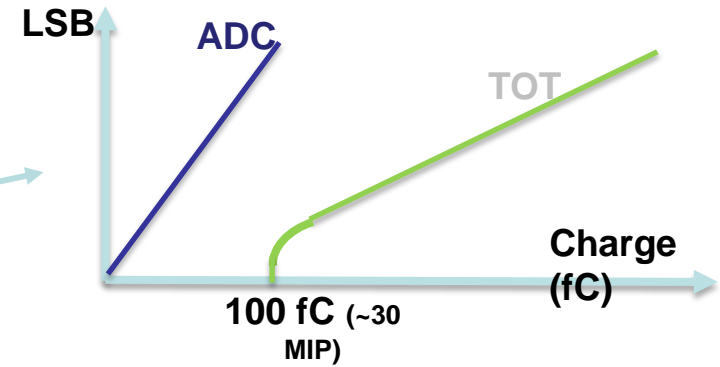
POWER CONSUMPTION

Preamplifiers (positive / negative)	5,3 mW / 5,6 mW
Slow shapers	1,94 mW
ToT	0,1 mW
ToA	2,6 mW
TDC	1,93 mW
Total analog (/channel)	12 – 13 mW

Assuming 20mW power dissipation for the digital part, we expect 850 mW for the entire chip

3 possibilities for sums:

- ❑ Analog sum: cost = 1 ADC / 4 channels
- ❑ Full range Digital sums: cost 1 LUT / channel
 - ❑ Correct for TOT non linearity
 - ❑ Correct different slopes
- ❑ ADC(s) range Digital sums:
 - ❑ up to 30 MIP in baseline
 - ❑ Up to 300 MIP in bi-gain (HG/LG factor of 2)



	Range	Sum precision	Extra ADC	Extra LUT power
A-sums	Full	++	16	0
Full D-sums	Full	++++	0	64
ADC D-sums (baseline)	30 MIP	+	0	0
ADC D-sums (bi-gain)	300 MIP	+++	0	0

For sums, mapping sensor cell to ASIC channel is done on PCB

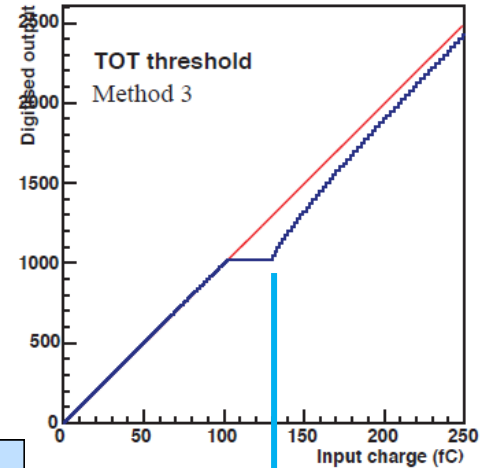
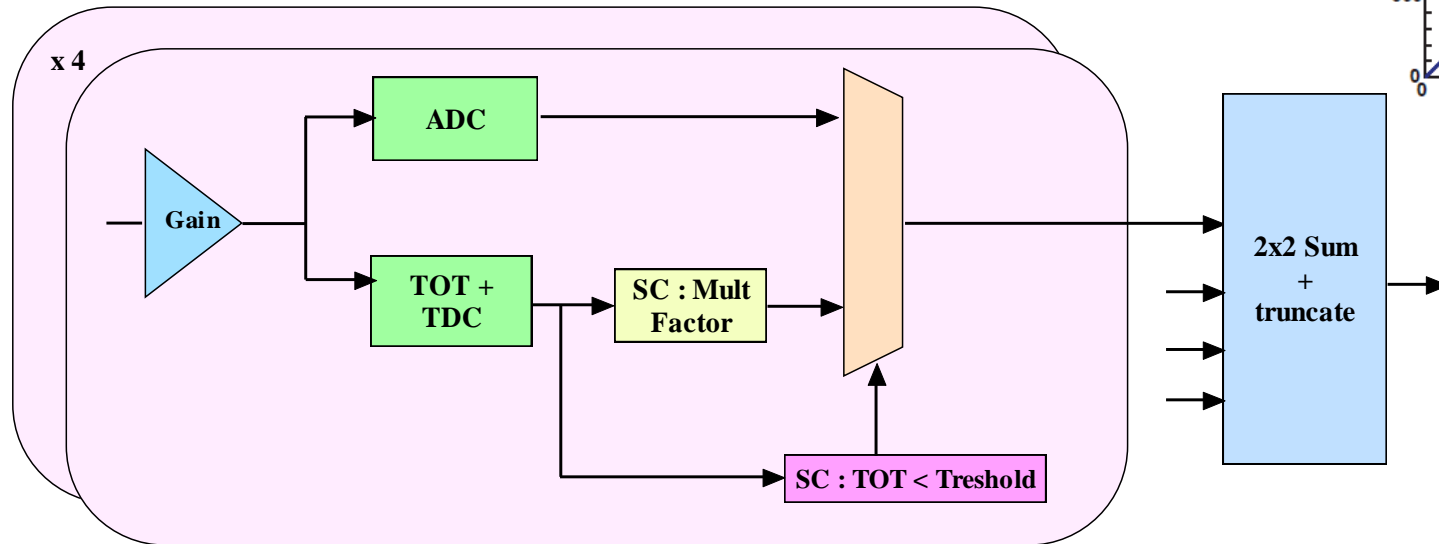
- ❑ Could have 2x2 / 4x4 sums (if adjacent channels ex:0-3 and 4-7)
- ❑ Adding extra mapping/confirmation in ASIC may add complexity / power consumption

Bandwidth: (dedicated slide ?) TP + DATA

Architecture for “method3”

Block inputs:

- Charge → ADC and TOT
- Multiplication factor (SC) → needed to have the same slope between ADC / TOT (0 to 1 with step 2^{-k})
- TOT Threshold (SC) → to remove TOT data below it



Threshold

2x2 Sum
+
truncate

Mult Factor:

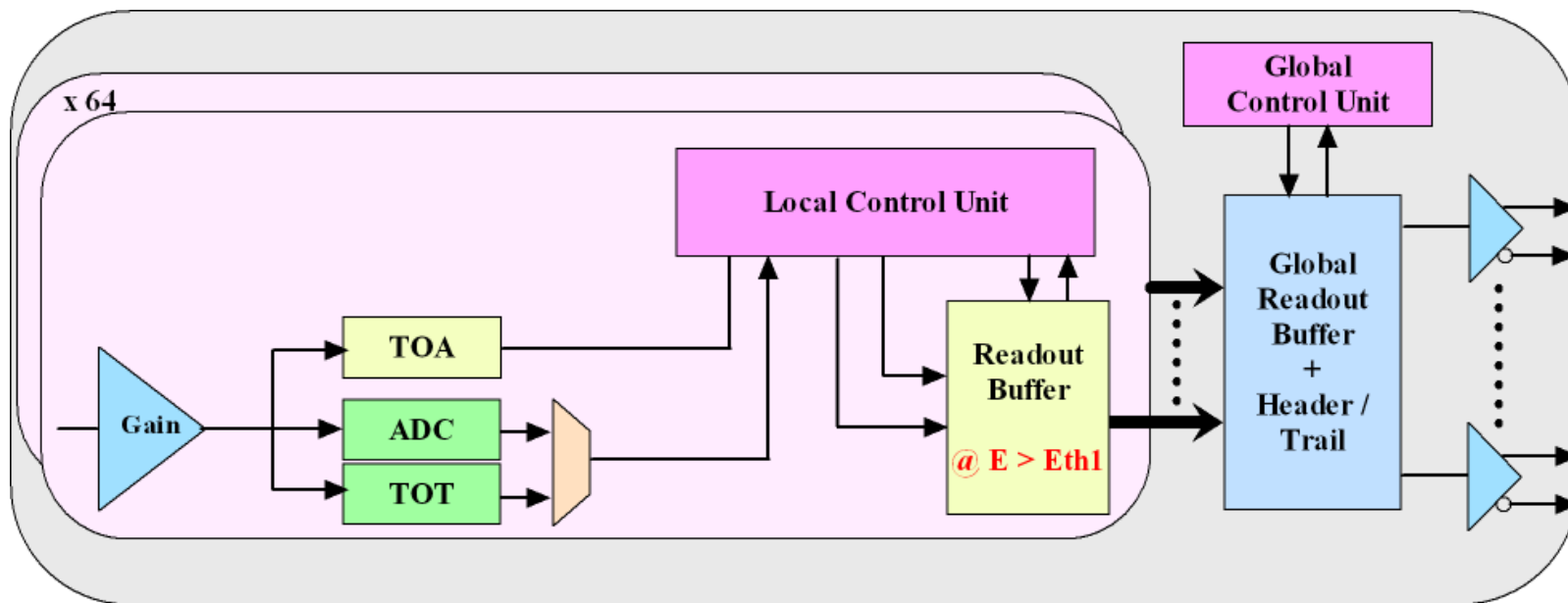
$$\sum_{k=0}^n a_k \cdot 2^{-k}$$

Design and simulation:

- VHDL block written, simulated and synthesized
- Full process takes about **15 ns** (post synthesis)
- Next steps: estimate **power/timing** vs **multiplication factor precision**
- Easily adaptable to all “method” (except 2) + Baseline & Bi-Gain architecture

Trigger: 40MHz readout architecture

- ❑ 64-channel ASIC with 0-suppress (see Philippe talk @ Engineering days):
 - ❑ 1 bit for empty cells
 - ❑ $E > E_{thr1}$, register ADC
 - ❑ $E > E_{thr2}$, register ADC + TOA



1MHz
readout

- ❑ Trigger logic / mapping done outside
- ❑ Reduction of buffers inside FE
- ❑ Increase Bandwidth / chip
- ❑ Power balance should be estimated

